

## Automotive-grade dual N-channel 40 V, 5 mΩ typ., 40 A STripFET™ F7 Power MOSFET in a PowerFLAT™ 5x6 DI

Datasheet - production data

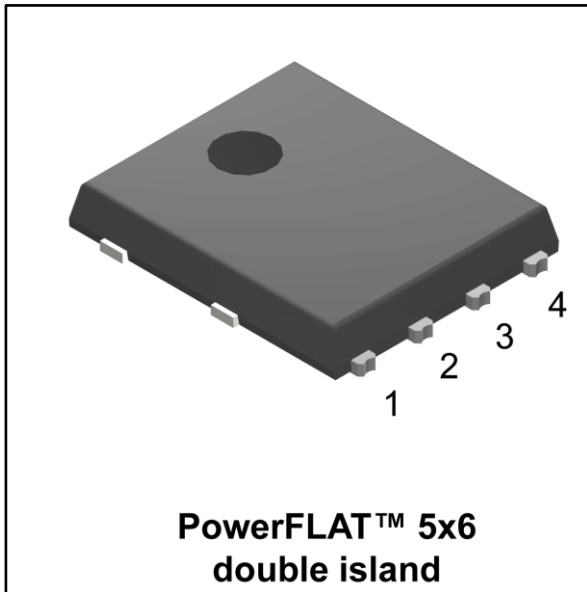


Figure 1: Internal schematic diagram

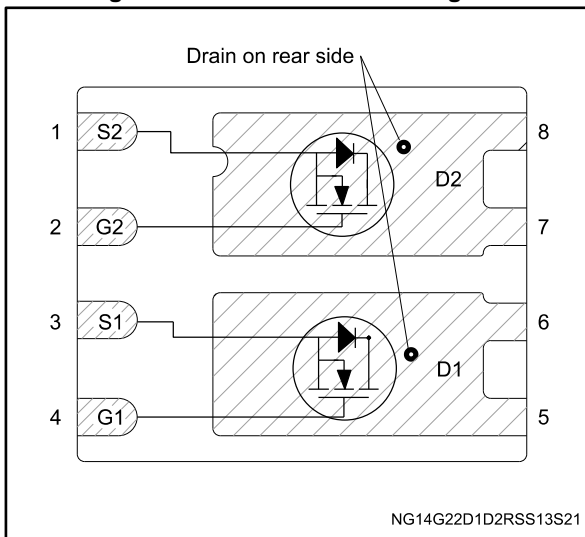


Table 1: Device summary

Order code	Marking	Package	Packing
STL76DN4LF7AG	76DN4LF7	PowerFLAT™ 5x6 double island	Tape and reel

### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STL76DN4LF7AG	40 V	6 mΩ	40 A



- AEC-Q101 qualified
- Among the lowest R<sub>DS(on)</sub> on the market
- Excellent FoM (figure of merit)
- Low C<sub>rss</sub>/C<sub>iss</sub> ratio for EMI immunity
- High avalanche ruggedness
- Wettable flank package

### Applications

- Switching applications

### Description

This dual N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	40	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	40	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	40	A
$I_{DM}^{(2)}$	Drain current (pulsed)	160	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	71	W
$T_j$	Operating junction temperature range	-55 to 175	$^\circ\text{C}$
$T_{stg}$	Storage temperature range		

**Notes:**

<sup>(1)</sup>Drain current is limited by package, the current capability of the silicon is 79 A at 25 °C and 56 A at 100 °C.

<sup>(2)</sup>Pulse width limited by safe operating area.

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	2.1	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	32	$^\circ\text{C}/\text{W}$

**Notes:**

<sup>(1)</sup>When mounted on FR-4 board of 1 inch<sup>2</sup>, 2oz Cu,  $t < 10\text{ s}$ .

## 2 Electrical characteristics

( $T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified)

**Table 4: On/Off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0\text{ V}$	40			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ $V_{DS} = 40\text{ V}$			10	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	1.5		2.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 10\text{ A}$		5	6	m $\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 10\text{ A}$		7	12	

**Table 5: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	956	-	pF
$C_{oss}$	Output capacitance		-	241	-	
$C_{rss}$	Reverse transfer capacitance		-	28	-	
$Q_g$	Total gate charge	$V_{DD} = 20\text{ V}$ , $I_D = 20\text{ A}$ , $V_{GS} = 0\text{ to }10\text{ V}$ (see <a href="#">Figure 14: "Test circuit for gate charge behavior"</a> )	-	17	-	nC
$Q_{gs}$	Gate-source charge		-	3.2	-	
$Q_{gd}$	Gate-drain charge		-	4.3	-	

**Table 6: Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 32\text{ V}$ , $I_D = 10\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 13: "Test circuit for resistive load switching times"</a> and <a href="#">Figure 18: "Switching time waveform"</a> )	-	9	-	ns
$t_r$	Rise time		-	4.3	-	
$t_{d(off)}$	Turn-off delay time		-	39	-	
$t_f$	Fall time		-	10	-	

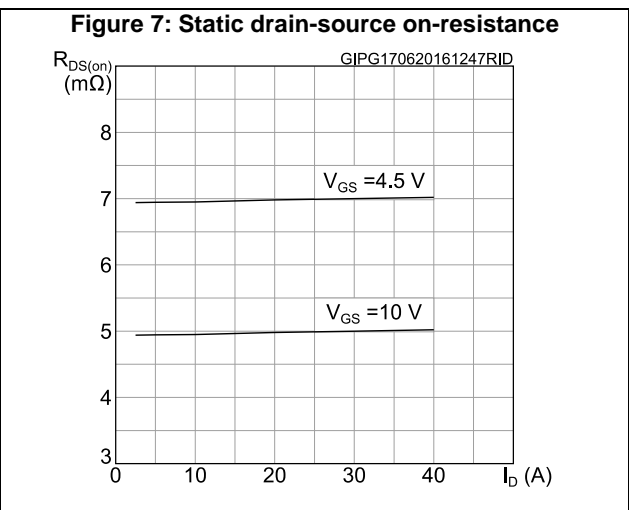
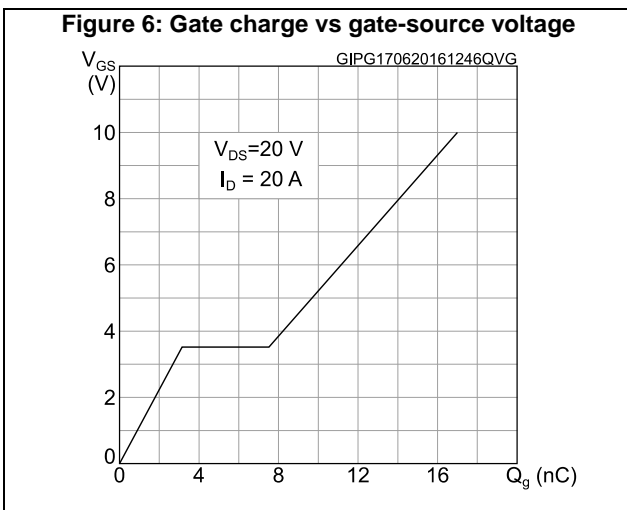
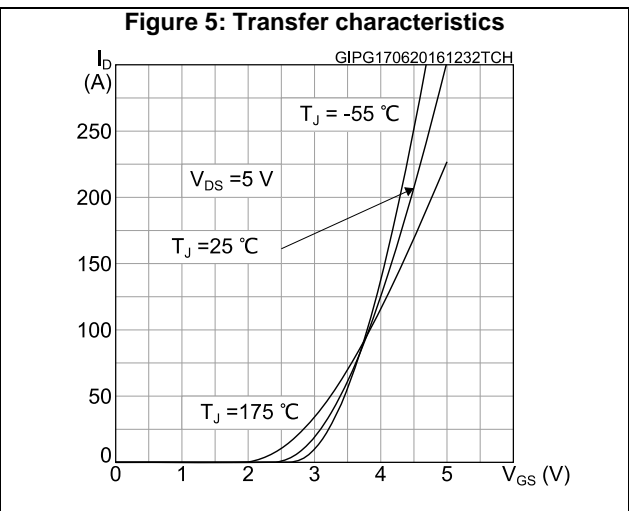
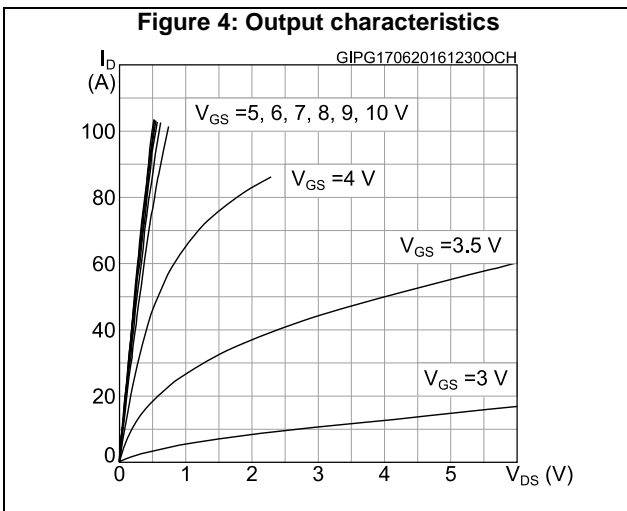
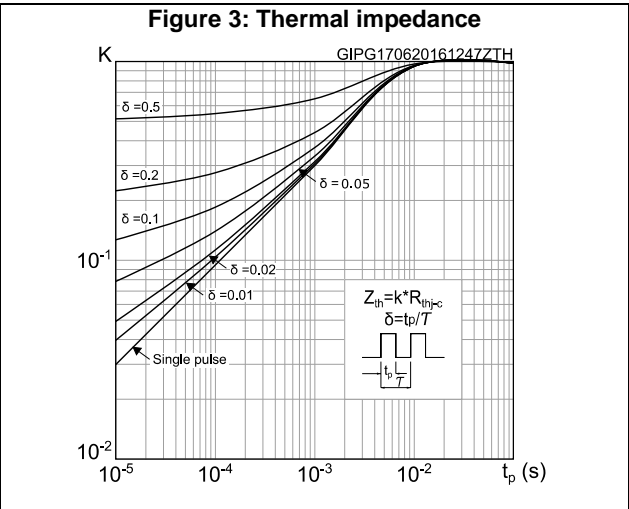
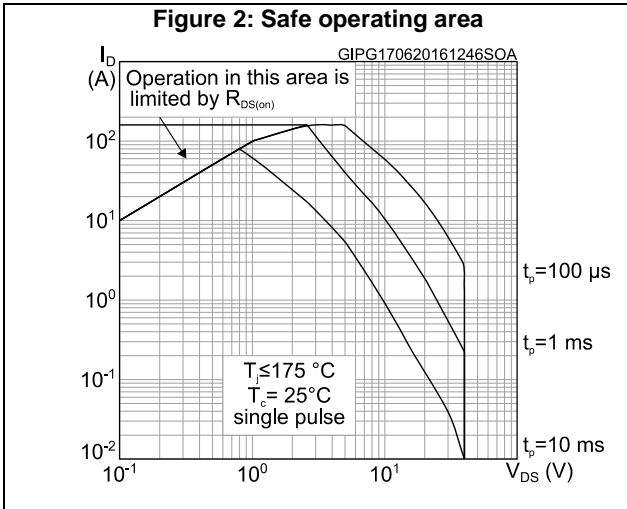
Table 7: Source-drain diode

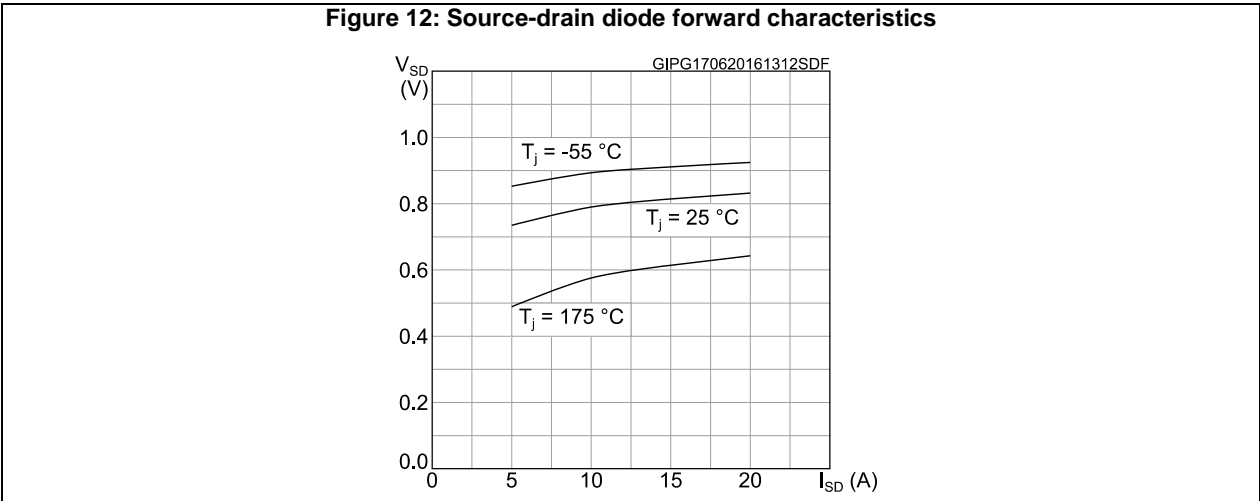
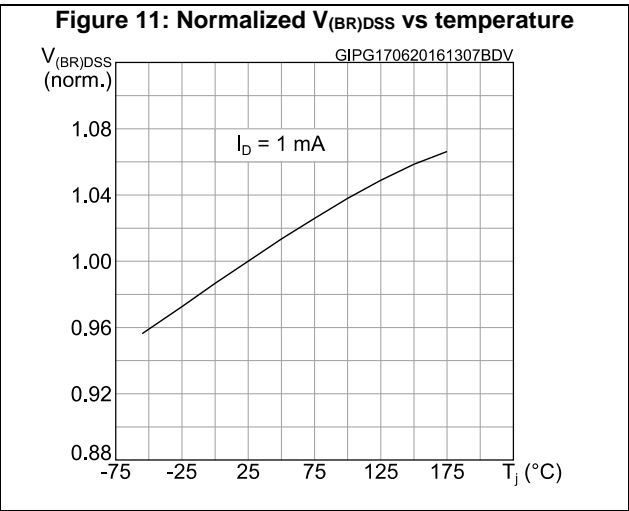
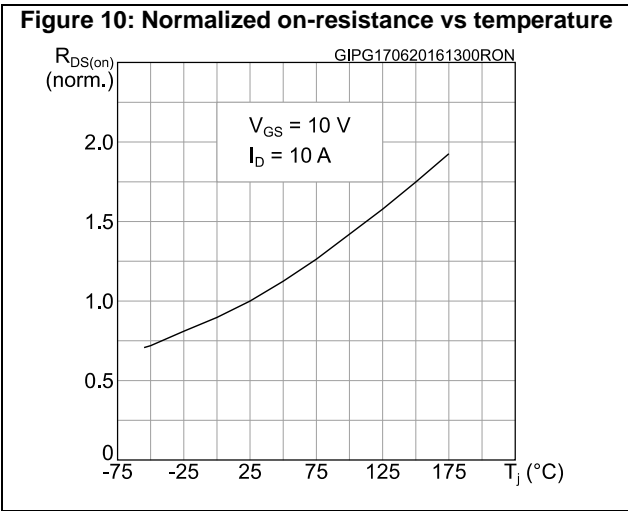
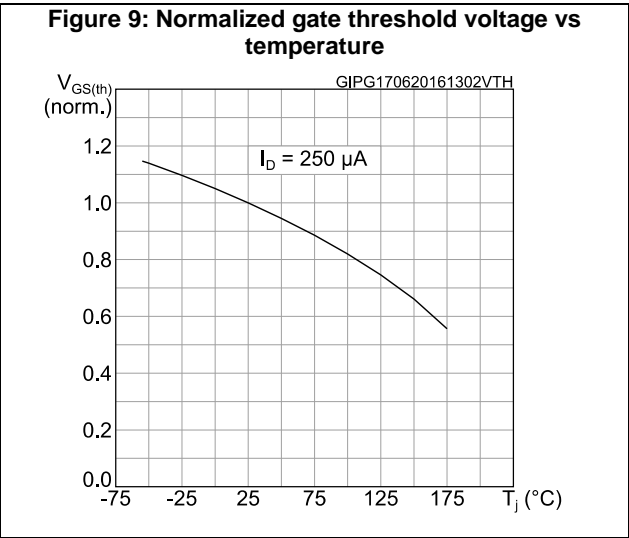
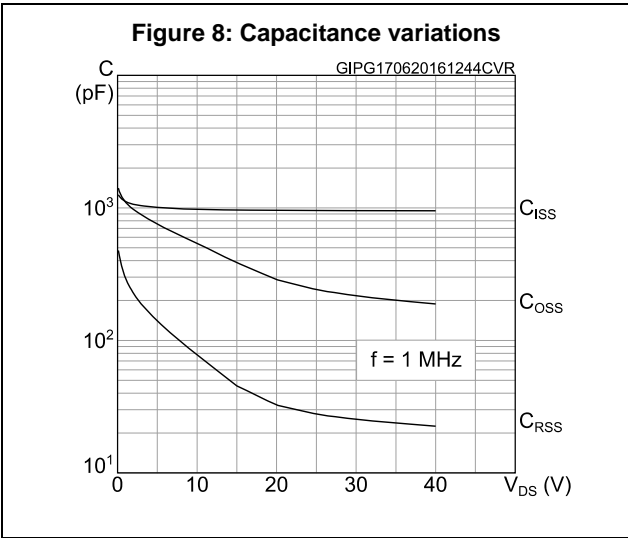
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		40	A
$I_{SDM}^{(2)}$	Source-drain current (pulsed)		-		160	A
$V_{SD}^{(3)}$	Forward on voltage	$I_{SD} = 40 \text{ A}$ , $V_{GS} = 0 \text{ V}$	-		1.3	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 20 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $V_{DD} = 32 \text{ V}$ (see <a href="#">Figure 15: "Test circuit for inductive load switching and diode recovery times"</a> )	-	27		ns
$Q_{rr}$	Reverse recovery charge		-	19.5		nC
$I_{RRM}$	Reverse recovery current		-	1.4		A

**Notes:**

- (1) Drain current is limited by package, the current capability of the silicon is 79 A at 25 °C.
- (2) Pulse width limited by safe operating area .
- (3) Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

## 2.1 Electrical characteristics (curves)





### 3 Test circuits

**Figure 13: Test circuit for resistive load switching times**



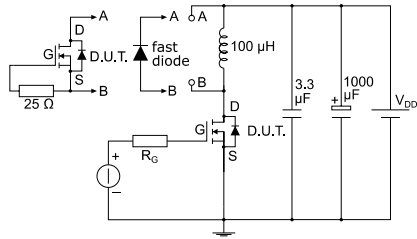
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**Figure 14: Test circuit for gate charge behavior**



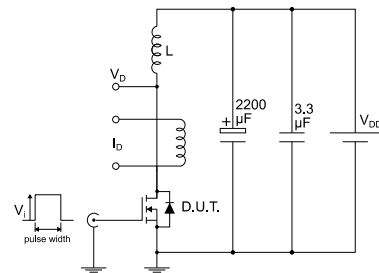
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**Figure 15: Test circuit for inductive load switching and diode recovery times**



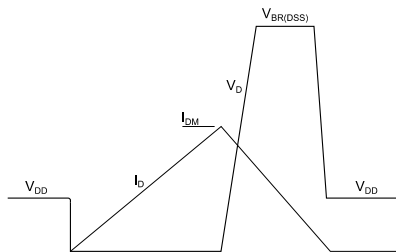
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**Figure 16: Unclamped inductive load test circuit**



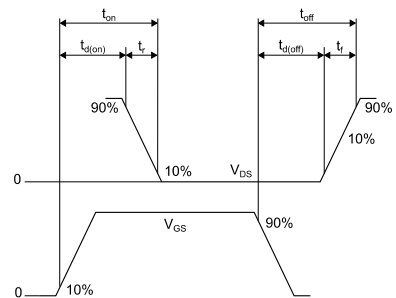
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**Figure 17: Unclamped inductive waveform**



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**Figure 18: Switching time waveform**



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## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.



Table 8: PowerFLAT™ 5x6 double island WF type C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
C	5.80	6.00	6.10
D	5.00	5.20	5.40
D2	4.15		4.45
D3	4.05	4.20	4.35
D4	4.80	5.00	5.10
D5	0.25	0.40	0.55
D6	0.15	0.30	0.45
D7	1.68		1.98
e		1.27	
E	6.20	6.40	6.60
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
E6	0.20	0.325	0.45
E7	0.85	1.00	1.15
E8	0.55		0.75
E9	4.00	4.20	4.40
E10	3.55	3.70	3.85
L	0.90	1.00	1.10
L1	0.175	0.275	0.375
K	1.05		1.35
Θ	0°		12°

Figure 20: PowerFLAT™ 5x6 double island recommended footprint (dimensions are in mm)

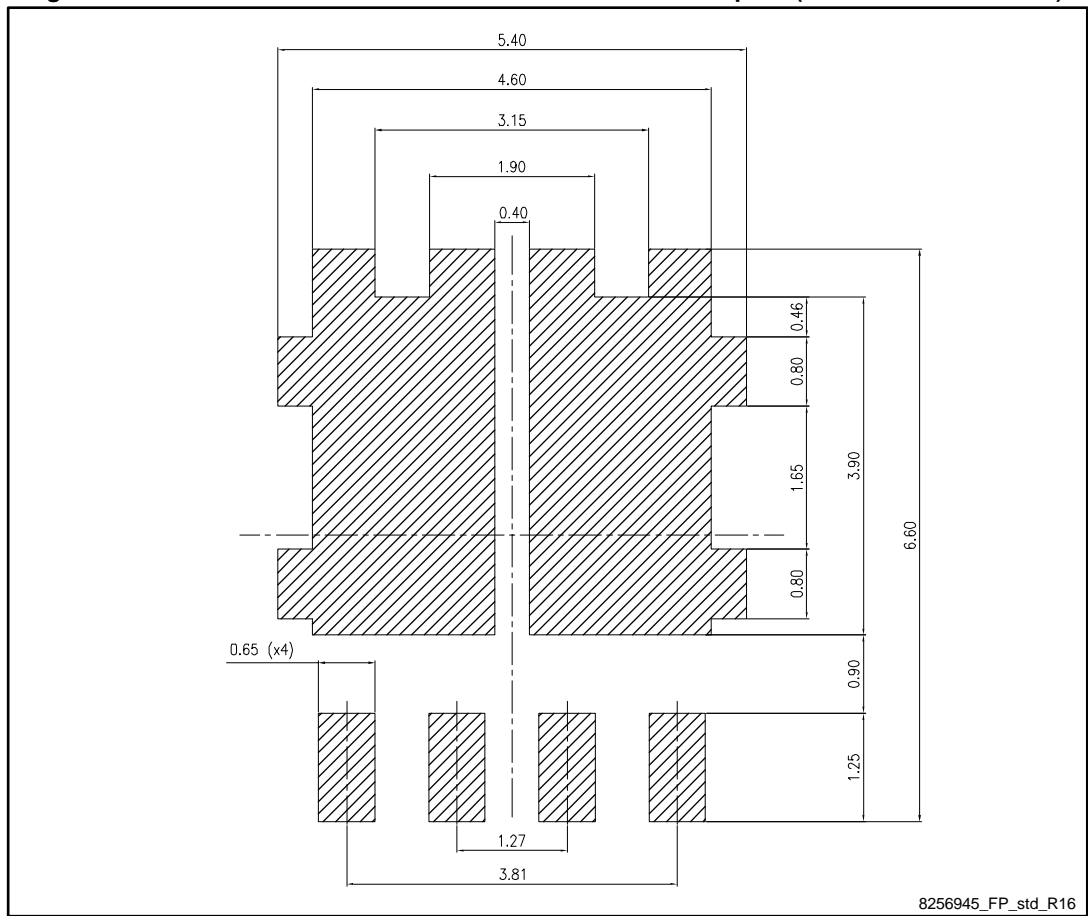
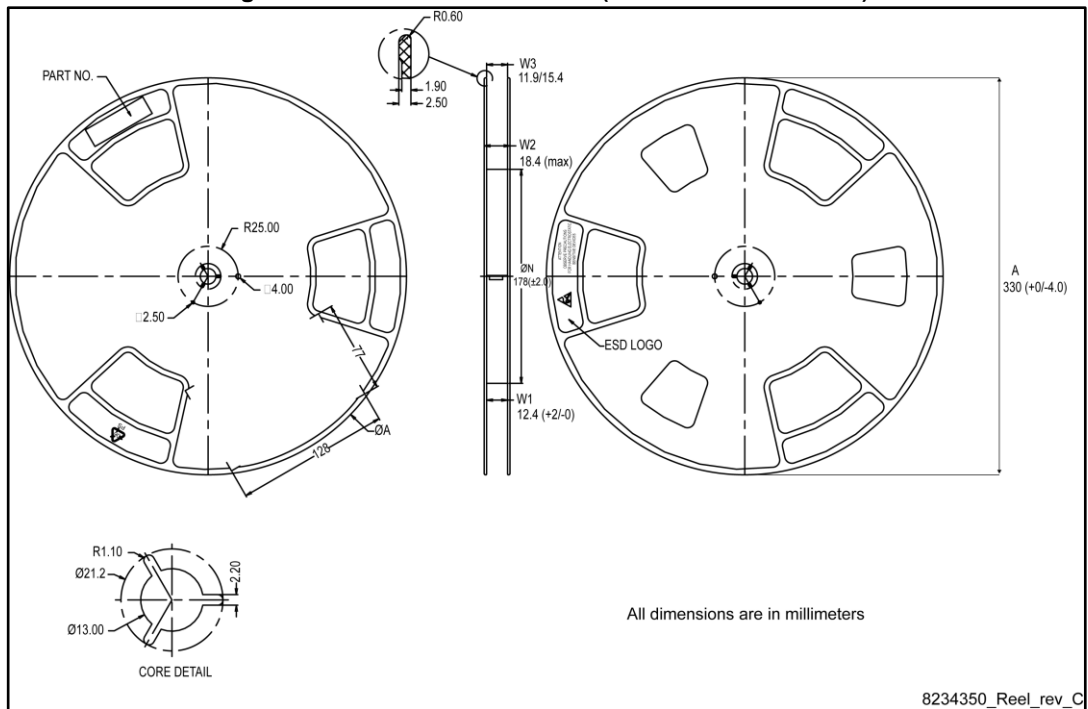




Figure 23: PowerFLAT™ 5x6 reel (dimensions are in mm)



## 5 Revision history

**Table 9: Document revision history**

Date	Revision	Changes
20-Apr-2016	1	First release.
23-Jun-2016	2	Modified: title, features and description in cover page. Modified: <i>Table 4: "On/Off states"</i> , <i>Table 5: "Dynamic"</i> , <i>Table 6: "Switching times"</i> and <i>Table 7: "Source-drain diode"</i> . Added: <i>Section 4.1: "Electrical characteristics (curves)"</i> . Updated: <i>Section 6.1: "PowerFLAT 5x6 double island WF type C package information"</i> . Minor text changes
27-Jul-2016	3	Updated <i>Table 4: "On/Off states"</i> .
16-Dec-2016	4	Updated <i>Section 4: "Package information"</i> . Minor text changes
27-Jul-2017	5	Updated title and features in cover page. Document status updated from preliminary to production data.

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